REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED

REV																									
SHEET																									
REV																									
SHEET																									
REV STATUS OF SHEETS	REV																								
	SHEET	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15									

PMIC N/A

STANDARDIZED MILITARY DRAWING

THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE

AMSC N/A

PREPARED BY: Larry T. Gauder

CHECKED BY: Thomas L. Reeves

APPROVED BY: [signature]

DRAWING APPROVAL DATE: 5 MARCH 1990

REVISION LEVEL:

DEFENSE ELECTRONICS SUPPLY CENTER
DAYTON, OHIO 45444

MICROCIRCUIT, DIGITAL, ADVANCED CMOS OCTAL D-TYPE FLIP-FLOP WITH THREE-STATE OUTPUTS, MONOLITHIC SILICON

SIZE	CAGE CODE	
A	67268	5962-89658

SHEET 1

DESC FORM 193
SEP 87

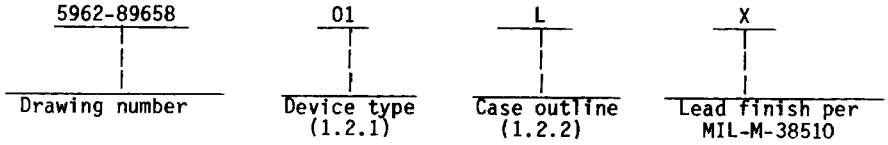
* U.S. GOVERNMENT PRINTING OFFICE: 1987 — 748-129/60911

5962-E1292

1. SCOPE

1.1 Scope. This drawing describes device requirements for class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices".

1.2 Part number. The complete part number shall be as shown in the following example:



1.2.1 Device types. The device types shall identify the circuit function as follows:

Device type	Generic number	Circuit function
01	54ACT534	Octal D-type flip-flop, with three-state outputs, TTL compatible inputs
02	54ACT11534	Octal D-type flip-flop, with three-state outputs, TTL compatible inputs

1.2.2 Case outlines. The case outlines shall be as designated in appendix C of MIL-M-38510, and as follows:

Outline letter	Case outline
L	D-9 (24-lead, 1.280" x .310" x .200"), dual-in-line package
R	D-8 (20-lead, 1.060" x .310" x .200"), dual-in-line package
S	F-9 (20-lead, .540" x .300" x .100"), flat package
2	C-2 (20-terminal, .358" x .358" x .100"), square chip carrier package
3	C-4 (28-terminal, .460" x .460" x .100"), square chip carrier package

1.3 Absolute maximum ratings.

Supply voltage range 1/	-0.5 V dc to +6.0 V dc
DC input voltage 1/	-0.5 V dc to V_{CC} + 0.5 V dc
DC output voltage 1/	-0.5 V dc to V_{CC} + 0.5 V dc
Input clamp diode current	±20 mA
Output clamp diode current	±50 mA
DC V_{CC} or GND current (per pin)	±100 mA
Storage temperature range	-65°C to 150°C
Maximum power dissipation (P_D)	500 mW
Lead temperature (soldering, 10 seconds)	+300°C
Thermal resistance, junction-to-case (θ_{JC})	See MIL-M-38510, appendix C
Junction temperature (T_J) 2/	+175°C

1.4 Recommended operating conditions.

Supply voltage range (V_{CC})	+4.5 V dc to +5.5 V dc
Input voltage range	0.0 V dc to V_{CC}
Output voltage range	0.0 V dc to V_{CC}
Case operating temperature range (T_C)	-55°C to +125°C

1/ Unless otherwise specified, all voltages are referenced to GND.
2/ Maximum junction temperature shall not be exceeded except for allowable short duration burn-in screening conditions in accordance with method 5004 of MIL-STD-883.

Input rise or fall times (t_r and t_f):	
V_{CC} = 4.5 V, 5.5 V	8 ns/V
Minimum setup time, Dn to CP (t_s):	
Device type 01:	
T_C = +25°C, V_{CC} = 4.5 V	4.5 ns
T_C = -55°C to +125°C, V_{CC} = 4.5 V	5.0 ns
Device type 02:	
T_C = +25°C, V_{CC} = 4.5 V	3.0 ns
T_C = -55°C to +125°C, V_{CC} = 4.5 V	3.0 ns
Minimum hold time, Dn to CP (t_h):	
Device type 01:	
T_C = +25°C, V_{CC} = 4.5 V	2.5 ns
T_C = -55°C to +125°C, V_{CC} = 4.5 V	3.0 ns
Device type 02:	
T_C = +25°C, V_{CC} = 4.5 V	5.5 ns
T_C = -55°C to +125°C, V_{CC} = 4.5 V	5.5 ns
Minimum pulse width, CP (t_w):	
Device type 01:	
T_C = +25°C, V_{CC} = 4.5 V	5.0 ns
T_C = -55°C to +125°C, V_{CC} = 4.5 V	5.0 ns
Device type 02:	
T_C = +25°C, V_{CC} = 4.5 V	9.0 ns
T_C = -55°C to +125°C, V_{CC} = 4.5 V	9.0 ns
Maximum frequency (f_{max}):	
Device type 01:	
T_C = +25°C, V_{CC} = 4.5 V	95 MHz
T_C = -55°C to +125°C, V_{CC} = 4.5 V	85 MHz
Device type 02:	
T_C = +25°C, V_{CC} = 4.5 V	55 MHz
T_C = -55°C to +125°C, V_{CC} = 4.5 V	55 MHz

2. APPLICABLE DOCUMENTS

2.1 Government specification, standard, and bulletin. Unless otherwise specified, the following specification, standard, and bulletin of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-M-38510 - Microcircuits, General Specification for.

STANDARD

MILITARY

MIL-STD-883 - Test Methods and Procedures for Microelectronics.

BULLETIN

MILITARY

MIL-BUL-103 - List of Standardized Military Drawings (SMD's).

(Copies of the specification, standard, and bulletin required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and herein.

3.2.1 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.2 Truth tables. The truth tables shall be as specified on figure 2.

3.2.3 Test circuit and switching waveforms. The test circuit and switching waveforms shall be as specified on figure 3.

3.2.4 Case outlines. The case outlines shall be in accordance with 1.2.2 herein.

3.3 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and shall apply over the full case operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.

3.5 Marking. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the part number listed in 1.2 herein. In addition, the manufacturer's part number may also be marked as listed in MIL-BUL-103 (see 6.6 herein).

3.6 Certificate of compliance. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in 6.6. The certificate of compliance submitted to DESC-ECS prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.

3.7 Certificate of conformance. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change. Notification of change to DESC-ECS shall be required in accordance with MIL-STD-883 (see 3.1 herein).

3.9 Verification and review. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. Sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions $-55°C < T_C < +125°C$ unless otherwise specified		Device type	Group A subgroups	Limits Min	Limits Max	Unit
High level output voltage	V_{OH}	V_{IN} = 2.0 V or 0.8 V I_{OH} = -50 µA 1/	V_{CC} = 4.5 V	All	1, 2, 3	4.4		V
			V_{CC} = 5.5 V			5.4		
		V_{IN} = 2.0 V or 0.8 V I_{OH} = -24 mA 1/	V_{CC} = 4.5 V			3.7		
			V_{CC} = 5.5 V			4.7		
		V_{IN} = 2.0 V or 0.8 V I_{OH} = -50 mA 1/	V_{CC} = 5.5 V			3.85		
Low level output voltage	V_{OL}	V_{IN} = 2.0 V or 0.8 V I_{OL} = 50 µA 1/	V_{CC} = 4.5 V	All	1, 2, 3		0.1	V
			V_{CC} = 5.5 V				0.1	
		V_{IN} = 2.0 V or 0.8 V I_{OL} = 24 mA 1/	V_{CC} = 4.5 V				0.5	
			V_{CC} = 5.5 V				0.5	
		V_{IN} = 2.0 V or 0.8 V I_{OL} = 50 mA 1/	V_{CC} = 5.5 V				1.65	
High level input voltage	V_{IH}	2/	V_{CC} = 4.5 V	All	1, 2, 3	2.0		V
			V_{CC} = 5.5 V			2.0		
Low level input voltage	V_{IL}	2/	V_{CC} = 4.5 V	All	1, 2, 3		0.8	V
			V_{CC} = 5.5 V				0.8	
Input leakage current	I_{IL}	V_{IN} = 0.0 V	V_{CC} = 5.5 V	All	1, 2, 3		-1.0	µA
	I_{IH}	V_{IN} = 5.5 V					1.0	

See footnotes at end of table.

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TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions $-55°C \le T_C \le +125°C$ unless otherwise specified	Device type	Group A subgroups	Limits Min	Limits Max	Unit
Maximum I_{CC} input current TTL inputs high	ΔI_{CC}	V_{CC} = 5.5 V, one input at 3.4 V, other inputs at GND or V_{CC}	All	1, 2, 3		1.6	mA
Quiescent current	I_{CCH}	V_{IN} = V_{CC} or GND, V_{CC} = 5.5 V	All	1, 2, 3		160	µA
	I_{CCL}					160	
	I_{CCZ}					160	
Off-state output leakage current	I_{OZH}	V_{IN} = 2.0 V or 0.8 V, V_{CC} = 5.5 V, V_{OUT} = V_{CC} or GND	All	1, 2, 3		10.0	µA
	I_{OZL}					-10.0	
Input capacitance	C_{IN}	See 4.3.1c	All	4		8.0	pF
Power dissipation capacitance	C_{PD}	See 4.3.1c 3/	01	4		50	pF
			02			115	
Functional tests		Tested at V_{CC} = 4.5 V and repeated at V_{CC} = 5.5 V, see 4.3.1d	All	7, 8			
Propagation delay time, CP to $\overline{Qn}$	t_{PHL}	V_{CC} = 4.5 V, R_L = 500Ω, C_L = 50 pF, see figure 3 4/	01	9	1.0	10.5	ns
				10, 11	1.0	13.0	
			02	9	1.5	13.3	
				10, 11	1.5	16.3	
	t_{PLH}		01	9	1.0	11.5	ns
				10, 11	1.0	14.0	
			02	9	1.5	12.7	
				10, 11	1.5	15.7	

See footnotes at end of table.

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TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions $-55°C < T_C < +125°C$ unless otherwise specified	Device type	Group A subgroups	Limits Min	Limits Max	Unit
Output enable time, $\overline{OE}$ to $\overline{Qn}$	t_{PZH}	V_{CC} = 4.5 V, R_L = 500Ω, C_L = 50 pF, see figure 3 4/	01	9	1.0	12.0	ns
				10, 11	1.0	14.0	
			02	9	1.5	12.0	
				10, 11	1.5	14.2	
	t_{PZL}		01	9	1.0	11.0	ns
				10, 11	1.0	13.0	
			02	9	1.5	12.2	
				10, 11	1.5	14.5	
Output disable time, $\overline{OE}$ to $\overline{Qn}$	t_{PHZ}		01	9	1.0	12.5	ns
				10, 11	1.0	14.5	
			02	9	1.5	12.9	
				10, 11	1.5	13.9	
	t_{PLZ}		01	9	1.0	10.5	ns
				10, 11	1.0	11.5	
			02	9	1.5	11.2	
				10, 11	1.5	12.5	

1/ The V_{OH} and V_{OL} tests will be tested at V_{CC} = 4.5 V. V_{CC} = 5.5 V will be guaranteed, if not tested to the limits in table I. Limits shown apply to operation at V_{CC} = 5.0 V ±0.5 V. Transmission driving tests are performed at V_{CC} = 5.5 V with a 2 ms duration maximum.

2/ The V_{IH} and V_{IL} tests are not required, and shall be used as forcing functions for the V_{OH} and V_{OL} tests.

3/ Power dissipation capacitance (C_{PD}), determines the dynamic power consumption, $P_D = (C_{PD} + C_L) V_{CC}^2 f$, and the dynamic current consumption (I_S) is, $I_S = (C_{PD} + C_L) V_{CC} f$.

4/ AC limits at V_{CC} = 5.5 V are equal to limits at V_{CC} = 4.5 V and guaranteed by testing at V_{CC} = 4.5 V. Minimum ac limits are guaranteed for V_{CC} = 5.5 V by guardbanding V_{CC} = 4.5 V limits to 1.5 ns (minimum).

Device type	01	02	
Case outlines	R, S, and 2	L	3
Terminal number	Terminal symbol		
1	$\overline{OE}$	$\overline{Q1}$	NC
2	$\overline{Q0}$	$\overline{Q2}$	V_{CC}
3	D0	$\overline{Q3}$	D4
4	D1	$\overline{Q4}$	D3
5	$\overline{Q1}$	GND	D2
6	$\overline{Q2}$	GND	D1
7	D2	GND	$\overline{OE}$
8	D3	GND	NC
9	$\overline{Q3}$	$\overline{Q5}$	$\overline{Q1}$
10	GND	$\overline{Q6}$	$\overline{Q2}$
11	CP	$\overline{Q7}$	$\overline{Q3}$
12	$\overline{Q4}$	$\overline{Q8}$	$\overline{Q4}$
13	D4	CP	GND
14	D5	D8	GND
15	$\overline{Q5}$	D7	NC
16	$\overline{Q6}$	D6	GND
17	D6	D5	GND
18	D7	V_{CC}	$\overline{Q5}$
19	$\overline{Q7}$	V_{CC}	$\overline{Q6}$
20	V_{CC}	D4	$\overline{Q7}$
21	---	D3	$\overline{Q8}$
22	---	D2	NC
23	---	D1	CP
24	---	$\overline{OE}$	D8
25	---	---	D7
26	---	---	D6
27	---	---	D5
28	---	---	V_{CC}

NC = No connection

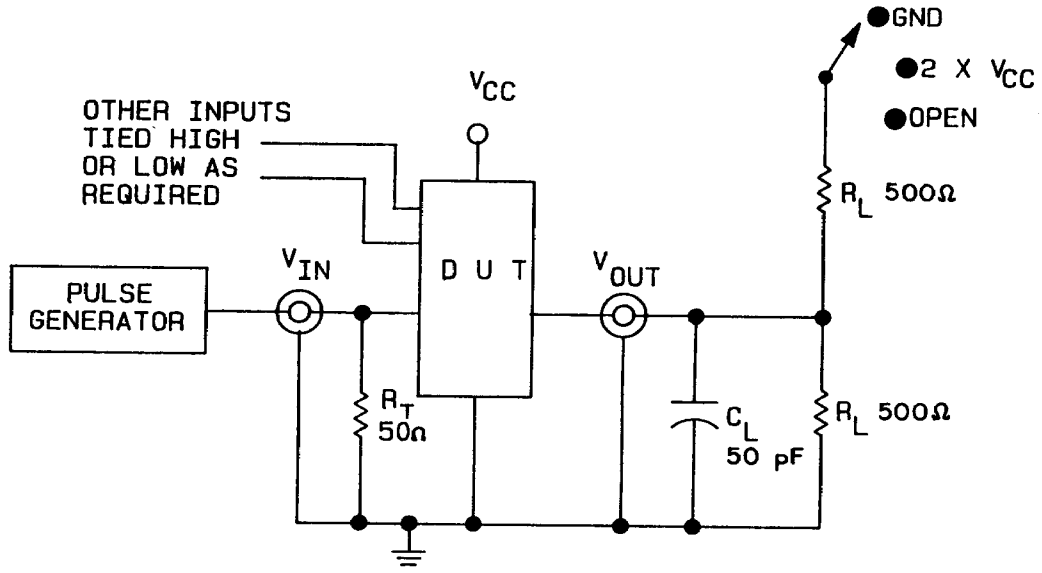
FIGURE 1. Terminal connections.

Inputs			Output
Dn	CP	$\overline{OE}$	$\overline{Qn}$
H	↑	L	L
L	↑	L	H
X	L	L	$\overline{Qo}$
X	X	H	Z

H = High voltage level
L = Low voltage level
Z = High impedance
X = Irrelevant
↑ = Low to high transition
$\overline{Qo}$ = Level of $\overline{Q}$ before the indicated steady-state input conditions were established.

FIGURE 2. Truth table.

THREE-STATE



Preferred method

GND = t_{PHZ} and t_{PZH}
2 x V_{CC} = t_{PLZ} and t_{PZL}
Open = t_{PLH} and t_{PHL}

Alternate method

Open = t_{PHZ}, t_{PZH}, t_{PLH}, and t_{PHL}
2 x V_{CC} = t_{PLZ} and t_{PZL}

NOTE: $t_r = t_f$ = 30 ns (10% to 90%) unless otherwise specified.

FIGURE 3. Test circuit and switching waveforms.

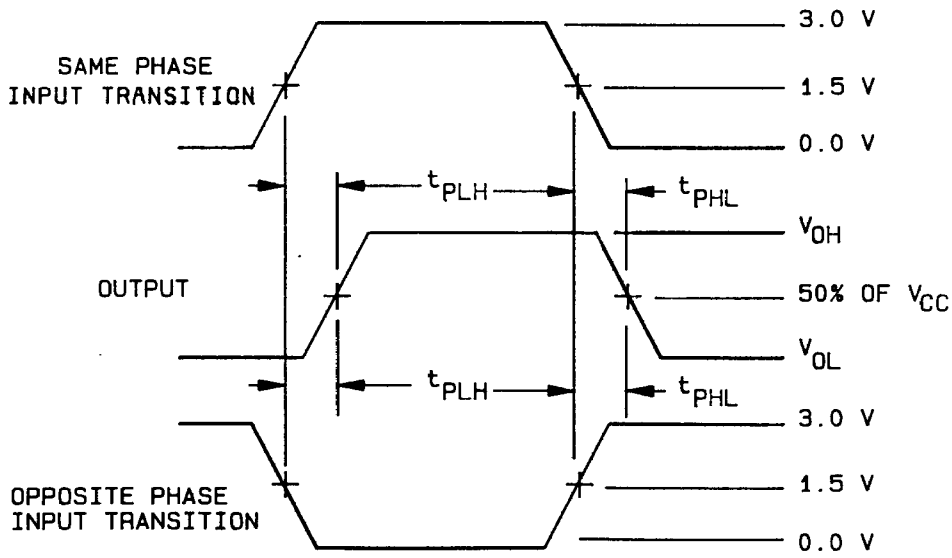


FIGURE 3. Test circuit and switching waveforms - Continued.

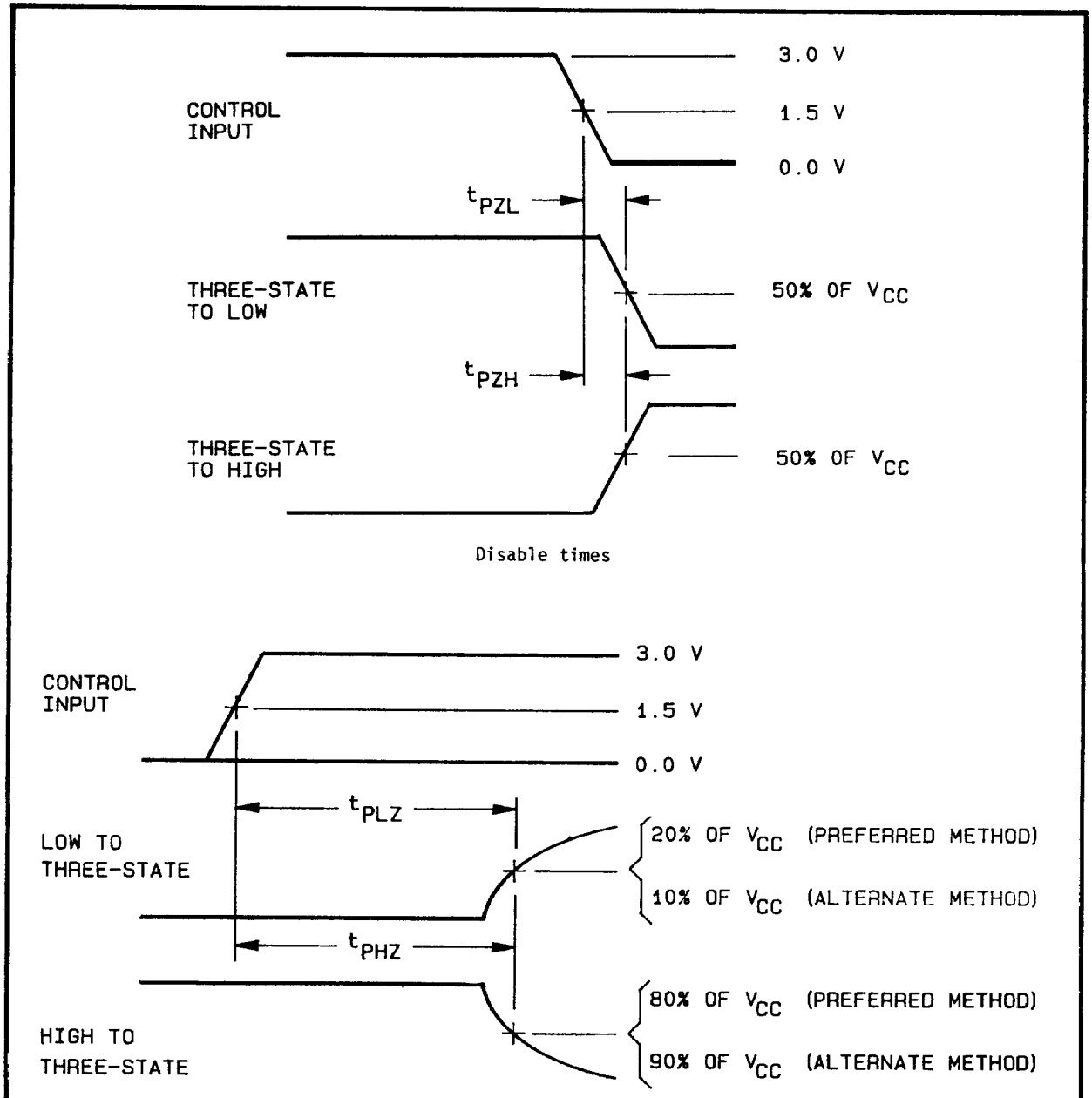


FIGURE 3. Test circuit and switching waveforms - Continued.

TABLE II. Electrical test requirements.

MIL-STD-883 test requirements	Subgroups (per method 5005, table I)
Interim electrical parameters (method 5004)	---
Final electrical test parameters (method 5004)	1*, 2, 3, 7, 8, 9
Group A test requirements (method 5005)	1, 2, 3, 4, 7, 8, 9, 10, 11
Groups C and D end-point electrical parameters method 5005	1,2,3

*PDA applies to subgroup 1.

4.2 Screening. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition A, B, C, or D using the circuit submitted with the certificate of compliance (see 3.6 herein).

(2) T_A = +125°C, minimum.

b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.

4.3 Quality conformance inspection. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.

4.3.1 Group A inspection.

a. Tests shall be as specified in table II herein.

b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.

c. Subgroup 4 (C_{IN} and C_{PD} measurements) shall be measured only for the initial test and after process or design changes which may affect capacitance. Test all applicable pins on five devices with zero failures.

d. Subgroups 7 and 8 tests shall verify the truth table as specified on figure 2.

4.3.2 Groups C and D inspections.

a. End-point electrical parameters shall be as specified in table II herein.

b. Steady-state life test conditions, method 1005 of MIL-STD-883.

(1) Test condition A, B, C, or D using the circuit submitted with the certificate of compliance (see 3.6 herein).

(2) T_A = +125°C, minimum.

(3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for OEM application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.

6.2 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.3 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-481 using DD Form 1693, Engineering Change Proposal (Short Form).

6.4 Record of users. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and the applicable SMD. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DESC-ECS, telephone (513) 296-6022.

6.5 Comments. Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone 513-296-5375.

6.6 Approved sources of supply. Approved sources of supply are listed in MIL-BUL-103. Additional sources will be added to MIL-BUL-103 as they become available. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-ECS. The approved sources of supply listed below are for information purposes only and are current only to the date of the last action of this document.

Military drawing part number	Vendor CAGE number	Vendor similar part number 1/
5962-8965801RX	27014	54ACT534DMQB
5962-8965801SX	27014	54ACT534FMQB
5962-89658012X	27014	54ACT534LMQB
5962-8965802LX	01295	SNJ54ACT11534JT
5962-89658023X	01295	SNJ54ACT11534FK

1/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number	Vendor name and address
01295	Texas Instruments, Incorporated 13500 N. Central Expressway P.O. Box 655303 Dallas, TX 75265 Point of contact: I-20 at FM1788 Midland, TX 79711-0448
27014	National Semiconductor 2900 Semiconductor Drive P.O. Box 58090 Santa Clara, CA 95052-8090 Point of contact: 333 Western Avenue South Portland, ME 04106